




BEST AVAILABLE COPY**Method for fabricating a phase shift mask**

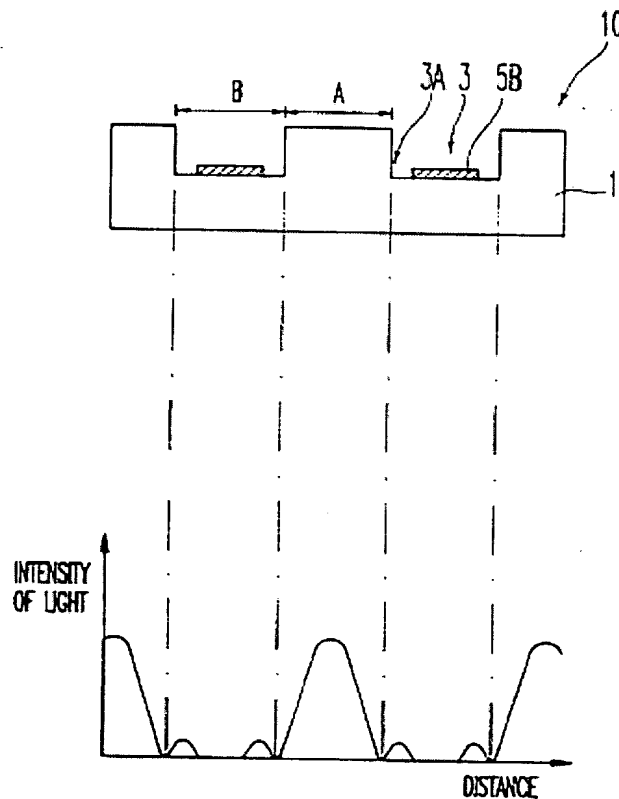
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A method for fabricating a phase shift mask is disclosed. In order to make the phase shift mask, an etching groove is formed on the light shielding portion of the quartz substrate and chrome is then formed on the center portion of the etching groove. The phase shift mask produces a phase shift effect without using phase shift materials, thereby increasing the optical contrast.



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